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Patent Number: EP0338251, B1

Publication date: 1989-10-25

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Requested Patent: JP1236657

Application Number: EP19890104703 19890316

Priority Number(s): JP19880064041 19880317

IPC Classification: H01L21/82; H01L27/06

EC Classification: H01L27/06D, H01L29/10D2, H01L21/338P2C, H01L21/8252

EC Classification: H01L27/06D; H01L29/10D2; H01L21/338P2C; H01L21/8252

Equivalents: DE68922653D, DE68922653T, KR9300603

Abstract

A semiconductor device which comprises a semi-insulating substrate (1) and a plurality of field effect transistors (FETs) formed on the semi-insulating substrate (1). An epitaxial layer (2) of one conductivity type is formed on the semi-insulating substrate by a crystal growth technique which is capable of controlling a film thickness at an atomic level. At least some of channel active layers of the FETs have different threshold voltages one another due to a difference in thickness of the epitaxial layer (2) and/or due to an additional ion implantation region selectively formed in the epitaxial layer (2). A manufacturing method of the semiconductor device is also disclosed, wherein a portion of the epitaxial layer (2) corresponding to the channel active layer of a FET is thickened by the repetition of an epitaxial growth, thinned by the etching of the epitaxial layer or ion implanted thereby obtaining a different threshold voltage from that of another FET.